



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

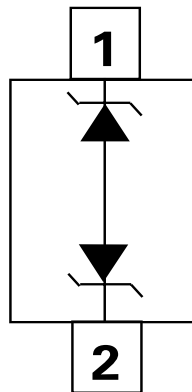
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



# SD-C Series 450W Discrete Bidirectional TVS Diode



## Pinout and Functional Block Diagram



## Description

The SD-C series can safely absorb repetitive ESD strikes at  $\pm 30\text{kV}$  (contact discharge, IEC 61000-4-2) without performance degradation and safely dissipate 30A (SD05C) of 8/20 $\mu\text{s}$  induced surge current (IEC 61000-4-5 2nd Edition) with very low clamping voltages.

## Features

- ESD, IEC 61000-4-2,  $\pm 30\text{kV}$  contact,  $\pm 30\text{kV}$  air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, IEC 61000-4-5 2nd Edition, 30A ( $t_p=8/20\mu\text{s}$ , SD05C)
- Low clamping voltage
- Low leakage current
- Small SOD323 package fits 0805 footprints
- AEC-Q101 qualified
- RoHS Compliant and Lead Free
- Moisture Sensitivity Level (MSL-1)

## Applications

- Switches / Buttons
- Test Equipment / Instrumentation
- Point-of-Sale Terminals
- Medical Equipment
- Notebooks / Desktops / Servers
- Computer Peripherals
- Automotive Electronics

## Additional Information



Datasheet



Resources



Samples

Life Support Note:

### Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

### Absolute Maximum Ratings

Symbol	Parameter	Value	Units
$P_{pk}$	Peak Pulse Power ( $t_p=8/20\mu s$ )	450	W
$T_{OP}$	Operating Temperature	-40 to 125	°C
$T_{STOR}$	Storage Temperature	-55 to 150	°C

Notes:

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### Thermal Information

Parameter	Rating	Units
Storage Temperature Range	-55 to 150	°C
Maximum Junction Temperature	150	°C
Maximum Lead Temperature (Soldering 20-40s)	260	°C

### SD05C Electrical Characteristics ( $T_{OP}=25^\circ C$ )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	$V_{RWM}$	$I_R \leq 1\mu A$			5.0	V
Reverse Voltage Drop	$V_R$	$I_R = 1mA$	6.0			V
Leakage Current	$I_{LEAK}$	$V_R = 5V$			1.0	$\mu A$
Clamp Voltage <sup>1</sup>	$V_C$	$I_{PP} = 1A, t_p = 8/20\mu s, Fwd$			10.0	V
		$I_{PP} = 10A, t_p = 8/20\mu s, Fwd$			14.5	V
Dynamic Resistance <sup>2</sup>	$R_{DYN}$	TLP, $t_p = 100ns$ , I/O to Ground		0.31		$\Omega$
Peak Pulse Current	$I_{PP}$	$t_p = 8/20\mu s$			30.0	A
ESD Withstand Voltage <sup>1</sup>	$V_{ESD}$	IEC61000-4-2 (Contact Discharge)	$\pm 30$			kV
		IEC61000-4-2 (Air Discharge)	$\pm 30$			kV
Diode Capacitance <sup>1</sup>	$C_D$	Reverse Bias=0V, f=1MHz			200	pF

### SD12C Electrical Characteristics ( $T_{OP}=25^\circ C$ )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	$V_{RWM}$	$I_R \leq 1\mu A$			12.0	V
Reverse Voltage Drop	$V_R$	$I_R = 1mA$	13.3			V
Leakage Current	$I_{LEAK}$	$V_R = 12V$			1.0	$\mu A$
Clamp Voltage <sup>1</sup>	$V_C$	$I_{PP} = 1A, t_p = 8/20\mu s, Fwd$			18.5	V
		$I_{PP} = 10A, t_p = 8/20\mu s, Fwd$			23.0	V
Dynamic Resistance <sup>2</sup>	$R_{DYN}$	TLP, $t_p = 100ns$ , I/O to Ground		0.41		$\Omega$
Peak Pulse Current	$I_{PP}$	$t_p = 8/20\mu s$			17.0	A
ESD Withstand Voltage <sup>1</sup>	$V_{ESD}$	IEC61000-4-2 (Contact Discharge)	$\pm 30$			kV
		IEC61000-4-2 (Air Discharge)	$\pm 30$			kV
Diode Capacitance <sup>1</sup>	$C_{D-GND}$	Reverse Bias=0V, f=1MHz			100	pF

**SD15C Electrical Characteristics (T<sub>Op</sub>=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V <sub>RWM</sub>	I <sub>R</sub> ≤ 1 μA			15.0	V
Reverse Voltage Drop	V <sub>R</sub>	I <sub>R</sub> = 1 mA	16.7			V
Leakage Current	I <sub>LEAK</sub>	V <sub>R</sub> = 15V			1.0	μA
Clamp Voltage <sup>1</sup>	V <sub>C</sub>	I <sub>PP</sub> = 1A, t <sub>p</sub> = 8/20 μs, Fwd			24.0	V
		I <sub>PP</sub> = 10A, t <sub>p</sub> = 8/20 μs, Fwd			31.0	V
Dynamic Resistance <sup>2</sup>	R <sub>DYN</sub>	TLP, tp = 100ns, I/O to Ground		0.46		Ω
Peak Pulse Current	I <sub>PP</sub>	t <sub>p</sub> = 8/20 μs			12.0	A
ESD Withstand Voltage <sup>1</sup>	V <sub>ESD</sub>	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance <sup>1</sup>	C <sub>I/O-GND</sub>	Reverse Bias = 0V, f = 1MHz			75	pF

**SD24C Electrical Characteristics (T<sub>Op</sub>=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V <sub>RWM</sub>	I <sub>R</sub> ≤ 1 μA			24.0	V
Reverse Voltage Drop	V <sub>R</sub>	I <sub>R</sub> = 1 mA	26.7			V
Leakage Current	I <sub>LEAK</sub>	V <sub>R</sub> = 24V			1.0	μA
Clamp Voltage <sup>1</sup>	V <sub>C</sub>	I <sub>PP</sub> = 1A, t <sub>p</sub> = 8/20 μs, Fwd			34.0	V
		I <sub>PP</sub> = 5A, t <sub>p</sub> = 8/20 μs, Fwd			42.0	V
Dynamic Resistance <sup>2</sup>	R <sub>DYN</sub>	TLP, tp = 100ns, I/O to Ground		0.62		Ω
Peak Pulse Current	I <sub>PP</sub>	t <sub>p</sub> = 8/20 μs			7.0	A
ESD Withstand Voltage <sup>1</sup>	V <sub>ESD</sub>	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance <sup>1</sup>	C <sub>I/O-GND</sub>	Reverse Bias = 0V, f = 1MHz			50	pF

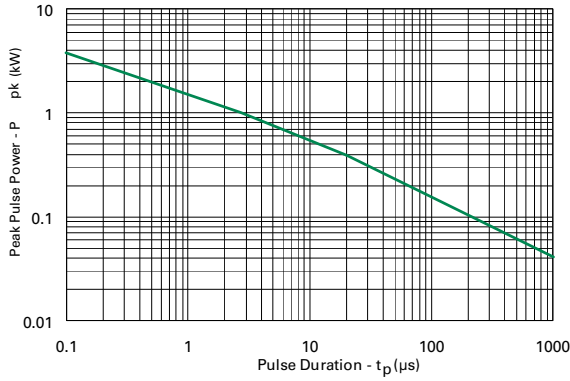
**SD36C Electrical Characteristics (T<sub>Op</sub>=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V <sub>RWM</sub>	I <sub>R</sub> ≤ 1 μA			36.0	V
Reverse Voltage Drop	V <sub>R</sub>	I <sub>R</sub> = 1 mA	40.0			V
Leakage Current	I <sub>LEAK</sub>	V <sub>R</sub> = 36V			1.0	μA
Clamp Voltage <sup>1</sup>	V <sub>C</sub>	I <sub>PP</sub> = 1A, t <sub>p</sub> = 8/20 μs, Fwd			50.0	V
		I <sub>PP</sub> = 4A, t <sub>p</sub> = 8/20 μs, Fwd			60.0	V
Dynamic Resistance <sup>2</sup>	R <sub>DYN</sub>	TLP, tp = 100ns, I/O to Ground		0.68		Ω
Peak Pulse Current	I <sub>PP</sub>	t <sub>p</sub> = 8/20 μs			5.0	A
ESD Withstand Voltage <sup>1</sup>	V <sub>ESD</sub>	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance <sup>1</sup>	C <sub>I/O-GND</sub>	Reverse Bias = 0V, f = 1MHz			30	pF

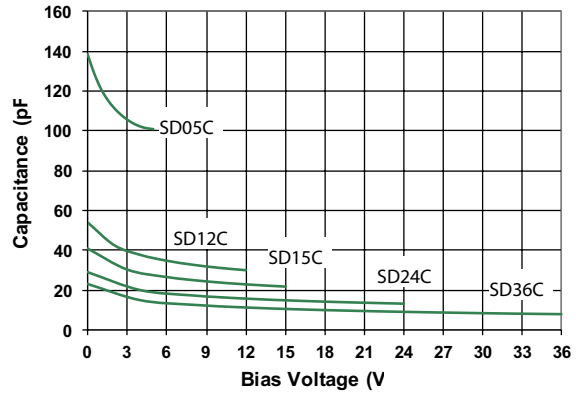
Note:

- Parameter is guaranteed by design and/or device characterization.
- Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

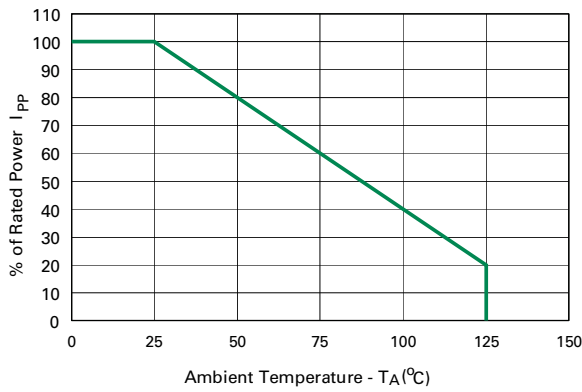
**Non-Repetitive Peak Pulse Power vs. Pulse Time**



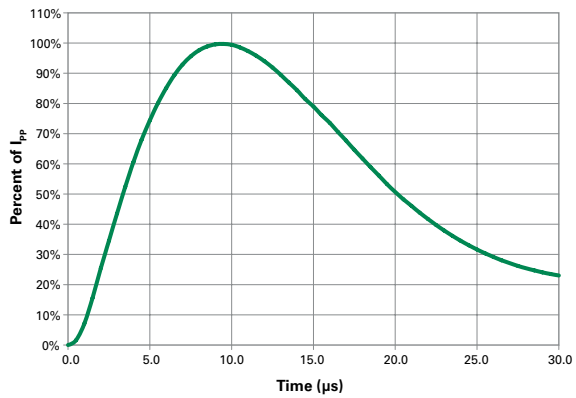
**Capacitance vs. Bias**



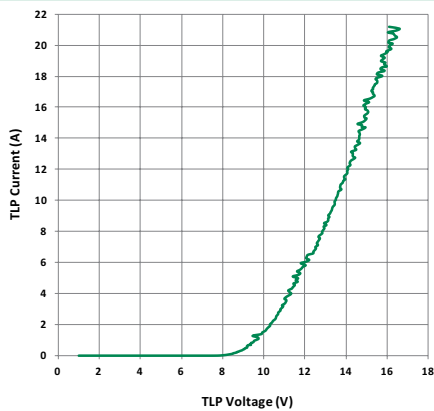
**Power Derating Curve**



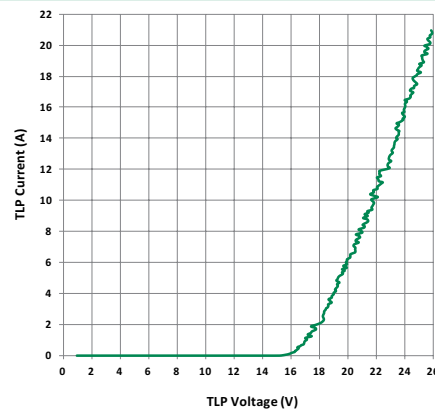
**8/20 μs Pulse Waveform**



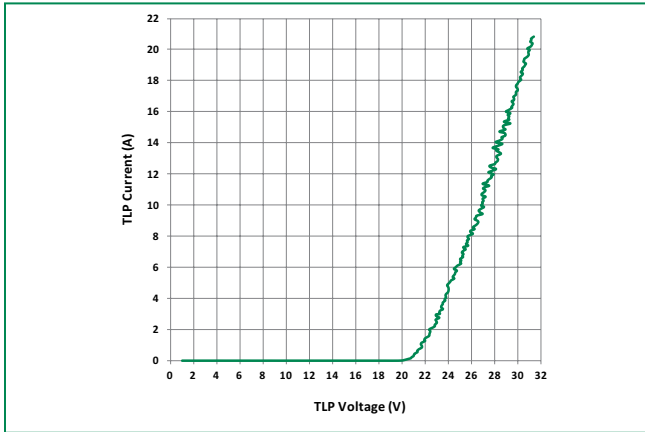
**SD05C Transmission Line Pulsing (TLP) Plot**



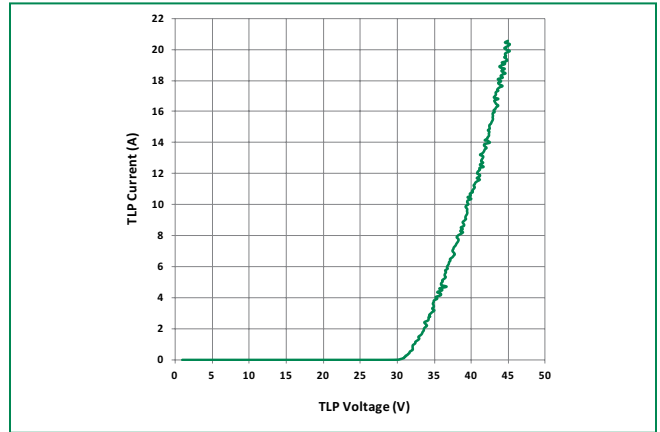
**SD12C Transmission Line Pulsing (TLP) Plot**



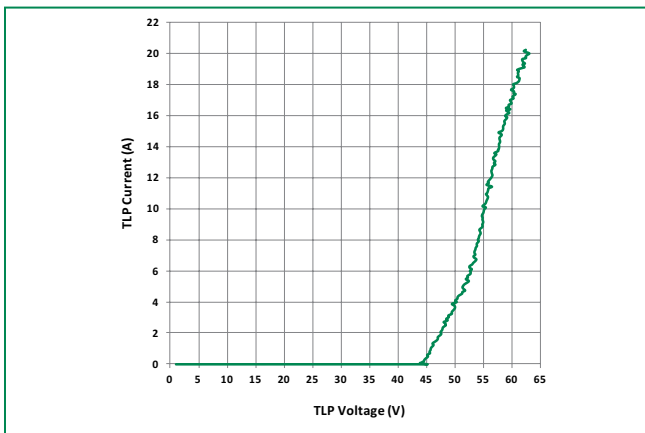
**SD15C Transmission Line Pulsing(TLP) Plot**



**SD24C Transmission Line Pulsing(TLP) Plot**

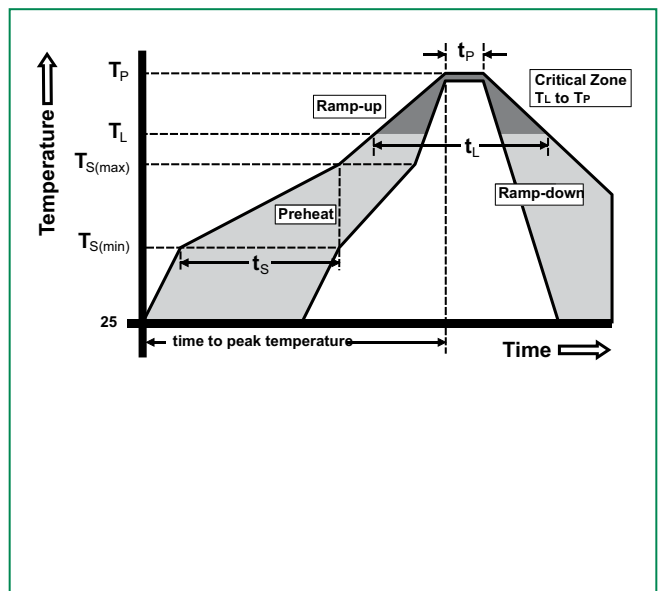


**SD36C Transmission Line Pulsing(TLP) Plot**



**Soldering Parameters**

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus) Temp ( $T_L$ ) to peak		3°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		260°C



### Product Characteristics

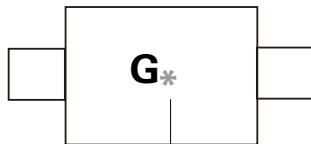
<b>Lead Plating</b>	Matte Tin
<b>Lead Material</b>	Copper Alloy
<b>Lead Coplanarity</b>	0.0004 inches (0.102mm)
<b>Substrate material</b>	Silicon
<b>Body Material</b>	V-0 per UL 94 Molded Epoxy

- Notes :
1. All dimensions are in millimeters
  2. Dimensions include solder plating.
  3. Dimensions are exclusive of mold flash & metal burr.
  4. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
  5. Package surface matte finish VDI 11-13.

### Ordering Information

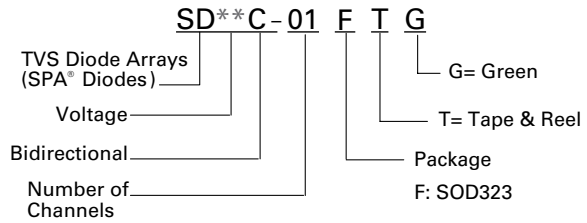
Part Number	Package	Marking	Min. Order Qty.
SD05C-01FTG	SOD323	G	3000
SD12C-01FTG	SOD323	G1	3000
SD15C-01FTG	SOD323	G2	3000
SD24C-01FTG	SOD323	G3	3000
SD36C-01FTG	SOD323	G4	3000

### Part Marking System

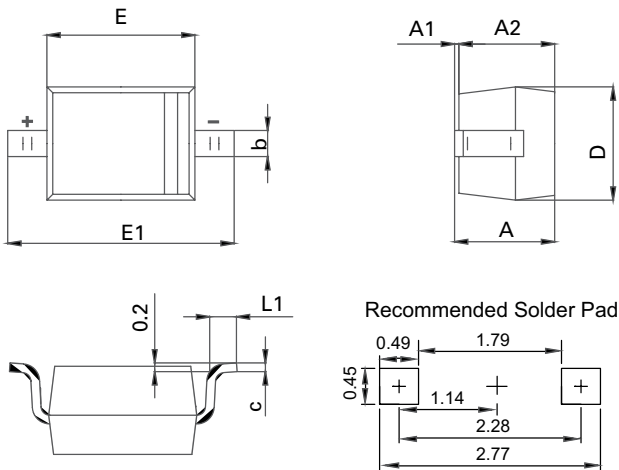


- Blank: SD05C-01FTG  
 1: SD12C-01FTG  
 2: SD15C-01FTG  
 3: SD24C-01FTG  
 4: SD36C-01FTG

### Part Numbering System



### Package Dimensions -SOD323



Unit: mm

Symbol	SOD323			
	Millimeters		Inches	
	Min	Max	Min	Max
<b>A</b>	0.8	1.14	0.031	0.045
<b>A1</b>	0.00	0.10	0.000	0.004
<b>A2</b>	0.80	1.04	0.031	0.014
<b>b</b>	0.25	0.35	0.010	0.014
<b>c</b>	0.08	0.15	0.003	0.006
<b>D</b>	1.15	1.45	0.045	0.057
<b>E</b>	1.60	1.90	0.063	0.075
<b>E1</b>	2.44	2.70	0.096	0.106
<b>L1</b>	0.25	0.45	0.010	0.018

**Embossed Carrier Tape & Reel Specification – SOD323**

